NSN 5961-01-241-2550

Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-241-2550 **Inclosure Material:** Metal **Overall Length:** 1.245 inches **Mounting Facility Quantity:** Joint Electronic Device Engineering Council/jedec/case Outline Designation: Do-4 **Electrode Internally-electrically Connected To Case:** Anode **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** 0.433 inches **Thread Size:** 0.190 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 400.0 repetitive peak reverse voltage **Current Rating Per Characteristic:** 12.00 milliamperes reverse current, peak **Power Rating Per Characteristic:** 15.0 kilowatts reverse power dissipation, instantaneous **Maximum Operating Tempurature Per Measurement Point:** 175.0 degrees celsius junction **Thread Series Designator:** Unf **Terminal Type And Quantity:** 1 tab, solder lug and 1 threaded stud Shelf Life: N/a **Unit Of Measure: Demilitarization:**

No **Fiig:**

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